

Strong coupling between a ferromagnetic contact and edge currents in a narrow HgTe quantum well

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We experimentally investigate spin-polarized electron transport between a permalloy ferromagnet and the edge of a two-dimensional electron system with band inversion, realized in a narrow HgTe quantum well. In zero magnetic field, we observe a strong asymmetry of the edge potential distribution with respect to the ferromagnetic ground lead. This result indicates the existence of a significant edge current, decoupled from the bulk 2DEG region, and a strong coupling between this edge channel and the ferromagnet due to the spin rotation at the interface.

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I. INTRODUCTION

Recently, there is a strong interest in two-dimensional semiconductor systems with an inverted band structure, like narrow HgTe and InAs/GaSb quantum wells. This interest is mostly connected with the quantum spin-Hall effect (QSHE) regime^{1,2} in zero magnetic field. Similarly to the conventional quantum Hall (QH) effect in high magnetic fields³, QSHE is characterized^{4,5} by presence of two spin-resolved, current-carrying edge states. These helical edge states are predicted to be counter-propagating ones at a particular sample edge⁶⁻⁹. In contrast, the conventional QH regime is characterized by chiral co-propagating edge states³. Experimental investigation of helical edge states is based on the charge transport along the edge, which has been detected in local and non-local resistance measurements^{1,2,4,5} and by a direct visualization technique¹⁰.

The edge transport is supposed to be essentially spin-dependent in two-dimensional systems with an inverted band structure⁶. On the other hand, spin effects are mostly prominent for the transport normal to the edge of the sample¹¹⁻¹³. For example, for a two-dimensional electron gas (2DEG) with strong spin-orbit coupling, the spin-Hall effect^{14,15} has been clearly demonstrated in semiconductor-ferromagnet hybrid structures¹⁶. In this experiment¹⁶, the ferromagnetic (F) leads realize the possibility of spin-polarized transport normal to the sample edge¹⁷, through the F-2DEG interface.

Here, we experimentally investigate spin-polarized electron transport between a permalloy ferromagnet and the edge of a two-dimensional electron system with band inversion, realized in a narrow HgTe quantum well. In zero magnetic field, we observe a strong asymmetry of the edge potential distribution with respect to the ferromagnetic ground lead. This result indicates the existence of a significant edge current, decoupled from the bulk 2DEG region, and a strong coupling between this edge channel and the ferromagnet due to the spin rotation at

the interface¹¹.

II. SAMPLES AND TECHNIQUE

Our $Cd_{0.65}Hg_{0.35}Te/HgTe/Cd_{0.65}Hg_{0.35}Te$ quantum wells with [013] surface orientations and width d of 8-8.3 nm are grown by molecular beam epitaxy. A detailed description of the sample structure is given elsewhere^{18,19}. Because of d above the critical value 6.3 nm, the quantum wells are characterized by band inversion^{2,5}. They contain a 2DEG with the electron density of $1.5 \cdot 10^{11} \text{cm}^{-2}$, as obtained from standard magnetoresistance measurements. The 2DEG mobility at 4K equals to $2 \cdot 10^5 \text{cm}^2/\text{Vs}$.

A sample sketch is presented in Fig. 1. A 200 nm high mesa step is formed by dry etching in Ar plasma. We fabricate f-2DEG junctions by using rf sputtering to deposit 50 nm thick ferromagnetic permalloy $Fe_{20}Ni_{80}$ stripes at the mesa step, with low (2-3 μm) overlap. The stripes are formed by lift-off technique, and the surface is mildly cleaned by Ar plasma before sputtering. To avoid any 2DEG degradation, the sample is not heated during the sputtering process. Two reference N-2DEG junctions N1 and N2 are obtained by thermal evaporation of 100 nm thick Au (yellow in Fig. 1). The width of each junction is equal to 20 μm .

Because of the insulating CdTe layer on the top of the structure, a side contact is formed between the metallic electrode and the 2DEG edge at the mesa step. In samples with etched mesa the edge potential profile is always smooth, so an insulating region of finite width is present at the 2DEG edge^{20,21}. In present samples this region is significant enough to provide highly resistive N-2DEG junctions, which corresponds to a tunnel transport regime with low (below 10^{-3}) transmission.

We study electron transport across one particular F-2DEG junction in two different three-point configurations I and II, see Fig. 1 (b-e): the corresponding fer-

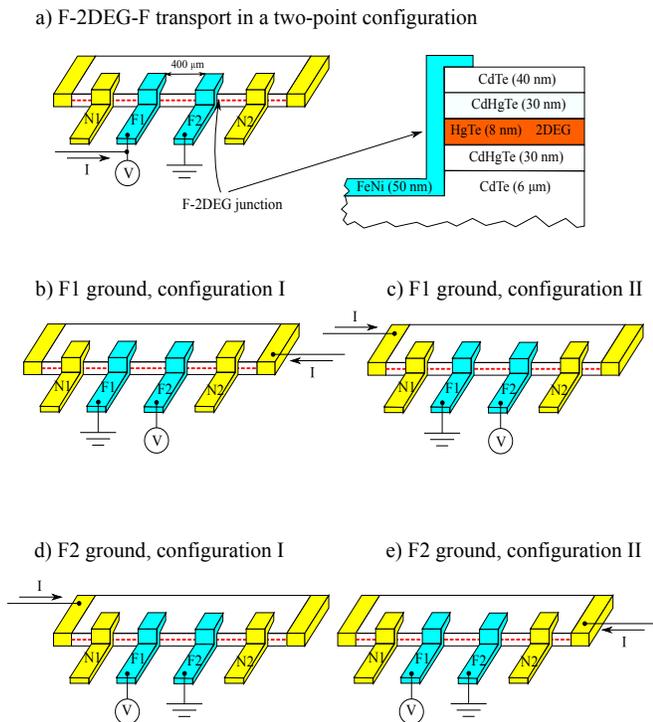


FIG. 1. (Color online) Sketch of the sample A (not in scale) with electrical connections in different experimental configurations. The $100\ \mu\text{m}$ wide mesa is formed by dry etching in Ar plasma. Two ferromagnetic $\text{Fe}_{20}\text{Ni}_{80}$ permalloy stripes (blue, F1 and F2) are placed at the mesa step, with low ($2\text{--}3\ \mu\text{m}$) overlap. In every overlap region, a side F-2DEG junction is formed between the ferromagnetic film and the 2DEG edge (denoted by a dashed line). The junctions F1 and F2 are separated by $400\ \mu\text{m}$ distance. Two reference N-2DEG junctions N1 and N2 are obtained by thermal evaporation of $100\ \text{nm}$ thick Au, as well as much wider ($100\ \mu\text{m}$) current contacts (yellow). We use the standard two-point F-2DEG-F configuration (a), realized by grounding the ferromagnetic stripe F2 and using F1 to apply a current and to measure a voltage drop simultaneously. We also study electron transport across the particular F-2DEG junction (grounded in (b-e)) in two different three-point configurations I and II. They differ by the position of a potential probe in respect to the current and ground ones. For the configuration I, the potential probe is placed in between them (b and d), while for the configuration II it is not the case (c and e).

romagnetic electrode is grounded; a current is applied between it and one of the normal contacts; another contact traces the 2DEG potential, all others are disconnected. The configurations I and II differ by the position of a potential probe with respect to the current and ground ones. For the configuration I, the potential probe is placed in between them, see Fig. 1 (b and d), while for the configuration II it is not the case (c and e). We also use the standard two-point F-2DEG-F configuration, realized by grounding one ferromagnetic stripe and using another to apply a current and to measure a voltage drop simultaneously, see Fig. 1 (a).

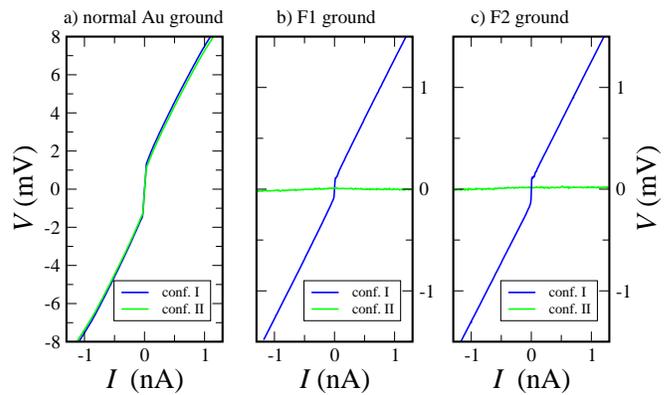


FIG. 2. (Color online) Examples of $I - V$ characteristics for two experimental configurations I and II. For a reference Au contact N1 (a) $I - V$ curves coincide well for both configurations I and II, so the result is independent on the particular choice of the current and voltage probes. For the ferromagnetic permalloy contacts F1 (b) or F2 (c), we obtain high-resistive (about $1\ \text{M}\Omega$) signal in the configuration I, while the signal is zero for the configuration II. Identical behavior is demonstrated for both contacts F1 and F2, so the observed effect is only determined by the mutual positions of current and voltage probes. The measurements are performed at a temperature of $30\ \text{mK}$ in zero magnetic field.

To obtain $I - V$ characteristics, depicted in Figs. 2 and 4, we sweep the dc current through the F-2DEG interface from $-1\ \text{nA}$ to $+1\ \text{nA}$ and measure the dc voltage in a mV range by using a dc electrometer. To obtain $dV/dI(I)$ characteristics in Fig. 5, this dc current is additionally modulated by a low ac component ($0.01\ \text{nA}$, $2\ \text{Hz}$). We measure the ac ($\sim dV/dI$) component of the 2DEG potential by using a lock-in with a high-impedance input preamplifier. We have checked, that the lock-in signal is independent of the modulation frequency in the range $1\ \text{Hz} - 6\ \text{Hz}$, which is defined by applied ac filters.

The measurements were performed at a temperature of $30\ \text{mK}$. To realize a spin-polarized transport¹⁶, the permalloy stripes were initially magnetized during sputtering. The sample was placed within a superconducting solenoid, which allows in situ control of the permalloy magnetization direction. We study several samples of the type A, which are depicted in Fig. 1, and one of the type B, where the central part (including both F-2DEG junctions) is additionally covered by a metallic gate, placed over a $350\ \text{nm}$ thick dielectric (guanine) layer. Qualitatively similar results were obtained from different samples in several cooling cycles, for different absolute values of junction resistances (in the range $0.4 - 1\ \text{M}\Omega$).

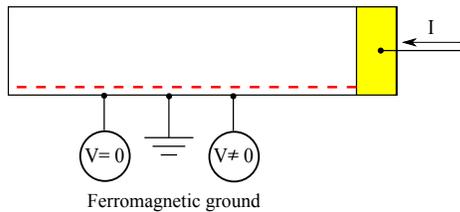


FIG. 3. (Color online) Summary of the experimental results, depicted in Fig. 2 (b-c). The ferromagnetic contact is grounded. We measure non-zero voltage only if the potential probe is placed in between the current and ground ones. The measured signal is zero if the potential probe is placed to the other side of the grounded contact. The observed effect is fully determined by the mutual positions of current and voltage probes with respect to the grounded ferromagnetic lead. In contrast, for a reference Au ground both potential probes measure identical signals, as depicted in Fig. 2 (a). Dashed line indicates the edge conductive channel, see Sec. IV

III. EXPERIMENTAL RESULTS

A. Single F-2DEG junction

Examples of $I - V$ characteristics are presented in Fig. 2. We ground a reference (normal) contact N1 (a) or one of two permalloy contacts F1 (b) or F2 (c). In every case the measurements are performed for two experimental configurations I and II.

We use a reference Au contact N1 to verify the experimental setup. As it is expected for a three-point technique, $I - V$ curves coincide well for both configurations I and II, see Fig. 2 (a). Because of the relatively low in-plane 2DEG resistance (below 1 k Ω at present 2DEG concentration and mobility), the 2DEG can be regarded as equipotential. The measured three-point $I - V$ curves in Fig. 2 (a) reflect the resistance of the grounded contact, so the result is to be independent on the particular choice of the current and voltage probes, as we see in Fig. 2 (a). The $I - V$ curves are obviously non-linear and are characterized by a high resistance (about 10 M Ω), which indicates a significant insulating region at the 2DEG edge^{20,21}.

Our most prominent experimental result is demonstrated in Fig. 2 (b-c). If we ground the permalloy ferromagnetic contact F1, the measured $I - V$ curve is crucially dependent on the mutual positions of current and voltage probes, see Fig. 2 (b). We obtain high-resistive signal in the configuration I, while the signal is zero in the configuration II. Identical behavior is demonstrated in Fig. 2 (c) for the grounded ferromagnetic contact F2. Thus, the observed effect is not connected with any absolute direction in the sample. It is also not connected with the current direction, since we obtain the same behavior for both current polarities in Fig. 2 (b-c). It is fully determined by the mutual positions of current and voltage probes with respect to the grounded ferromag-

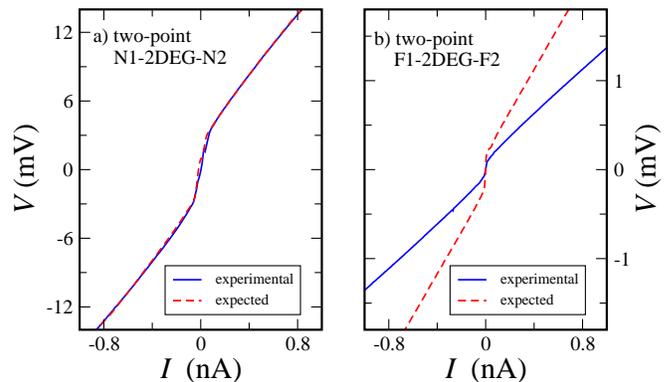


FIG. 4. (Color online) Two-point $I - V$ characteristics (solid) for the normal (a) double Au-2DEG-Au or the ferromagnetic (b) F-2DEG-F junctions in comparison with the expected $I - V$ dependencies (dash). The measured and the calculated $I - V$ curves coincide well for the reference Au-2DEG-Au junction (a). The experimental F-2DEG-F $I - V$ corresponds to a roughly two times smaller resistance, than it can be calculated from three-point $I - V$ characteristics of individual F-2DEG junctions in Fig. 2 (b-c). The measurements are performed at a temperature of 30 mK in zero magnetic field.

netic lead, as it is schematically depicted in Fig. 3. The effect has been confirmed for different samples. We wish to emphasize that this behavior is very unusual and is in a high contrast to the ordinary behavior of a three-point resistance of a reference Au contact in Fig. 2 (a).

The $I - V$ curves, obtained in the configuration I in Fig. 2 (b-c) are obviously non-linear. They look even quantitatively similar for two different contacts F1 and F2 and are characterized by a high, about 1 M Ω , resistance.

B. Double F-2DEG-F junctions

Asymmetry of potential distribution is obvious, e.g., in the QH regime in high magnetic fields. Similarly to usual QH approaches²², we measure $I - V$ characteristics in a two-point configuration, denoted as (a) in Fig. 1.

In this case, we should investigate in-series connected resistances of two junctions and a 2DEG region between them. For our samples, the latter value is relatively small (below 1 k Ω at present 2DEG concentration and mobility), so we naively could expect that the experimental $I - V$ in a two-point configuration is equal to a sum of two individual three-point $I - V$ s of the corresponding junctions. In the experiment, this expectation is precisely confirmed for a reference Au-2DEG-Au double junction, see Fig. 4 (a), but is obviously broken for the ferromagnetic contacts F1 and F2 (b).

The experimental two-point F-2DEG-F $I - V$ in Fig. 4 (b) corresponds to a roughly two times smaller resistance, than we could expect from the measurements of individual F-2DEG junctions in the configuration I, depicted in

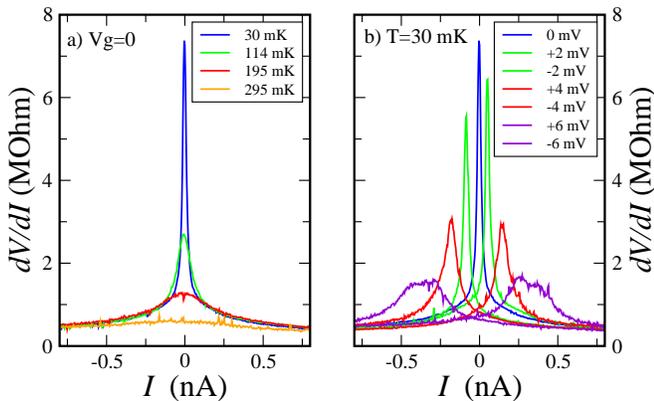


FIG. 5. (Color online) Two-point differential resistance dV/dI between two ferromagnetic leads (F1-2DEG-F2 junction) at low biases for the sample B with a metallic gate. The zero-bias resistance is suppressed by (a) temperature and (b) gate voltage. The curves in (b) panel are shifted horizontally to demonstrate the symmetrical suppression with respect to a gate voltage sign.

Fig. 2 (b-c). We wish to mention here, that the comparison is only reasonable for the configuration I, because of zero result in the configuration II. The experimental $I-V$ in Fig. 4 (b) is checked to be invariant if we exchange F1 and F2 contacts in this two-point configuration.

C. Temperature and gate-voltage dependencies

The curve obtained for the ferromagnetic contacts F1 and F2 in Fig. 4 (b) is perfectly antisymmetric. It is nonlinear and is characterized by a narrow high-resistive region at low biases. This behavior is demonstrated with high accuracy in Fig. 5 as two-point $dV/dI(I)$ dependencies for the sample B (with a metallic gate).

A temperature increase suppresses the zero-bias resistance, see Fig. 5 (a). The non-linearity in Fig. 5 (a) disappears completely above 0.3 K. In contrast, the linear branches of the $I-V$ curve are invariant below 1 K.

A gate voltage also suppresses this zero-bias non-linearity, see Fig. 5 (b). The effect is fully symmetric with respect to a gate voltage sign. The non-linearity is strongly suppressed at ± 6 mV gate bias, which has been checked to have no effect on the bulk carrier concentration. We are also sure that there is no noticeable gate leakage at least within ± 30 mV for our 350 nm thick guanine dielectric.

The initial magnetization of the permalloy is oriented within the 2DEG plane, but it can be changed by the external magnetic field. We do not see any effect of the magnetization direction, however, a magnetic field above 0.2 T sharply increases the zero-bias resistive region.

IV. DISCUSSION

The observed asymmetry in Fig. 2 (b-c) is not characteristic for the ferromagnetic side contacts to 2DEG structures without band inversion, cp. Ref 16. Since we have also verified our setup in different tests with normal (Au) leads, we should conclude that this behavior is the result of a combination of the spin-polarized ferromagnetic side contact and the edge of a 2DEG with band inversion.

Similarly to the standard QH regime^{3,22}, asymmetric edge potential distribution with respect to the grounded contact implies a significant edge current contribution, as depicted in Fig. 3. If we supposed solely the bulk current distribution, different signals in the configurations I and II would require a bulk 2DEG resistance to exceed strongly the F-2DEG contact contribution. Perfect asymmetry, depicted in Figs. 2 (b-c),3 is hardly possible for the side contacts even in this case, because of geometry. The measured resistance (above 1 M Ω) would correspond to a bulk charge-neutrality regime, where it is the edge transport that is well known to be dominant⁵. This is also inconsistent with a metallic bulk conductivity at $1.5 \cdot 10^{11} \text{cm}^{-2}$ electron concentration in our samples.

On the other hand, the edge current has been demonstrated to coexist with the conductive bulk by a direct visualization experiment¹⁰. The coexistence is also possible from the theoretical considerations^{6,23}, but requires a low coupling between the edges and the bulk, possibly because of the formation of a depletion region where the edge channel is laterally localized¹⁰, see Fig. 6. Thus, the edge-state transport in 2DEG structures with band inversion can also be important for a conductive bulk, in a crude similarity to the QH edge state transport in a dissipative regime between two neighbor QH plateaus²².

The edge structure is specifically important in our experiment, because we use side contacts to the mesa edge, in contrast to previous investigations.^{1,2,4,5} As it is known from the QH investigations^{20,24,25}, the edge profile is always smooth at the etched mesa edge: while approaching the sample edge, a local electron concentration is gradually diminishing from the bulk value to zero. In other words, the edge potential works similarly to a (local) top gate potential, so a depletion region of a finite width is always present at the sample edge^{20,21}, see Fig. 6. We can expect for the edge structure, depicted in Fig. 6, that a metallic side contact is coupled to both the conductive edge channel and to the bulk 2DEG.

Zero signal in the configuration II in Fig. 2 (b-c) indicates strong (mostly perfect) coupling between the ferromagnetic contact and the one-dimensional edge channel. In this case, the edge current is flowing along the shortest edge to the perfect ferromagnetic ground, so there is no edge current near the potential probe in the configuration II, see Fig. 3. The observed in Fig. 2 (b-c) asymmetry is therefore of a geometrical origin and the signal in the configuration I reflects the resistance of the edge channel at a macroscopic distance.

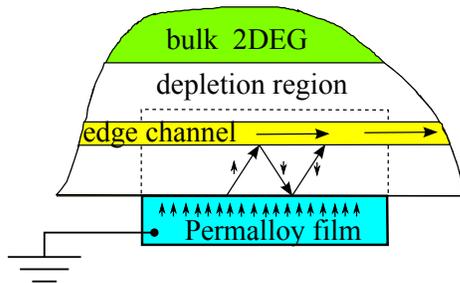


FIG. 6. (Color online) Top-view of the 2DEG region near the ferromagnetic contact. A formation of a depletion region is shown, where the edge current is laterally localized. For a spin-polarized electron flow (depicted by arrows) from the ferromagnetic contact, the reflected electron is characterized by the opposite spin projection, since the helical edge modes resonantly enhance the spin rotation¹¹. It can not be absorbed by the ferromagnetic contact because of the necessary absorption of a polarization component opposite to the permalloy magnetization. It is redirected back to the edge conductive channel, which results in the experimentally observed strong coupling between the edge channel and the ferromagnetic contact. Dashed line schematically indicates a vicinity of the contact, where the proximity magnetization is important.

This strong coupling to the edge channel has to be specifically spin-dependent process. It occurs only for a ferromagnetic contact, while the reference Au contacts in Figs. 2 (a), 4 (a) demonstrate a standard tunnel behavior. The coupling to the edge channel is not dominant in this case, so the measured $I - V$ s reflect mostly the resistance across the edge depletion region near the grounded contact²⁶.

From the continuous evolution of the edge current when the system is driven away from the charge-neutral regime, demonstrated in Ref. 10, we can suppose that the edge current is still carried by helical spin-resolved edge states, even for the conductive bulk. Strong coupling between the helical edge states and a ferromagnet can be anticipated from the theoretical considerations^{11,12}. In Refs. 11 and 12 it is predicted that an electron injected from the normal metal shows a spin-dependent reflection at the interface leading to the spin rotation. The spin rotation angle can be as large as π , because the helical edge modes resonantly enhance the spin rotation. The presence of the barrier at the interface does not destroy this effect, moreover, the helical edge mode becomes more important¹¹. In our case of a spin-polarized electron flow from the ferromagnetic contact, reflected electron can not be absorbed by a contact because of the necessary absorption of a polarization component opposite to the permalloy magnetization. Thus, we can expect enhanced tunneling to the helical edge modes, i.e. strong coupling between the helical edge states and a ferromagnet. This

coupling is obviously independent of the permalloy magnetization direction, because a ferromagnet locally aligns the spins of two helical edge states due to a proximity effect^{13,27} in the vicinity of the contact, as denoted by a dashed line in Fig. 6.

In the case of perfect coupling between the ferromagnetic contact and the one-dimensional edge channel, the signal in the configuration I in Fig. 2 (b-c) reflects mostly the resistance of the edge channel at a macroscopic distance, between the contacts F1 and F2. The same resistance is also measured in Fig. 4 (b) for a long F-2DEG-F junction, because of low contact contribution. It is not surprising therefore that all three $I - V$ curves in Figs. 2 (b-c), 4 (b) demonstrate even quantitatively identical behavior.

The linear $I - V$ branches in Figs. 2, 4 correspond to about $1 \text{ M}\Omega$, which is well known⁵ for a transport along the helical current-carrying states at macroscopic distances. They are invariant in Fig. 5, which is also consistent with the reported temperature and gate voltage behavior of the diffusive edge state transport in QSHE regime.²⁸ On the other hand, the narrow zero-bias resistive region in Figs. 2 (b-c), 5 has not been reported yet. We connect it with the necessary edge state structure reconstruction in the vicinity of a ferromagnetic contact (denoted by a dashed line in Fig. 6), because of the proximity magnetization¹³. This reconstruction is strongly affected by a low variation of a temperature and a gate potential, see Fig. 5 (a) and (b) respectively, but has no effect on the coupling to a contact itself, that provides zero signal in the configuration II even for lowest biases.

V. CONCLUSION

We experimentally investigate spin-polarized electron transport between a permalloy ferromagnet and the edge of a two-dimensional electron system with band inversion, realized in a narrow HgTe quantum well. In zero magnetic field, we observe a strong asymmetry of the edge potential distribution with respect to the ferromagnetic ground lead. This result indicates the existence of a significant edge current, decoupled from the bulk 2DEG region, and a strong coupling between this edge channel and the ferromagnet due to the spin rotation at the interface¹¹.

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